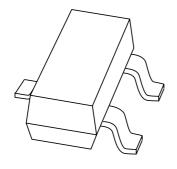
DISCRETE SEMICONDUCTORS

DATA SHEET



BAS29; BAS31; BAS35 General purpose controlled avalanche (double) diodes

Product data sheet Supersedes data of 2001 Oct 10 2003 Mar 20



General purpose controlled avalanche (double) diodes

BAS29; BAS31; BAS35

FEATURES

• Small plastic SMD package

• Switching speed: max. 50 ns

· General application

• Continuous reverse voltage: max. 90 V

• Repetitive peak reverse voltage: max. 110 V

· Repetitive peak forward current: max. 600 mA

• Repetitive peak reverse current: max. 600 mA.

APPLICATIONS

General purpose switching in e.g. surface mounted circuits.

DESCRIPTION

General purpose switching diodes fabricated in planar technology, and encapsulated in small rectangular plastic SMD SOT23 packages. The BAS29 consists of a single diode. The BAS31 has two diodes in series. The BAS35 has two diodes with a common anode.

MARKING

TYPE NUMBER	MARKING CODE(1)
BAS29	L20 or *A8
BAS31	L21 or *V1
BAS35	L22 or *V2

Note

* = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

PINNING

PIN	DESCRIPTION						
FIN	BAS29	BAS31	BAS35				
1	anode	anode	cathode (k1)				
2	not connected	cathode	cathode (k2)				
3	cathode	common connection	common anode				

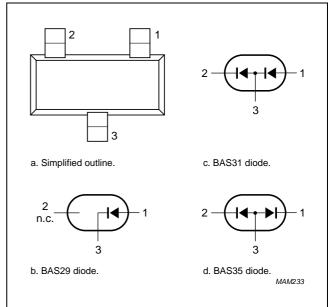


Fig.1 Simplified outline (SOT23) and symbols.

General purpose controlled avalanche (double) diodes

BAS29; BAS31; BAS35

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per diode						
V_{RRM}	repetitive peak reverse voltage		_	110	V	
V_R	continuous reverse voltage		_	90	V	
I _F	continuous forward current	single diode loaded; see Fig.2; note 1	_	250	mA	
		double diode loaded; see Fig.2; note 1	_	150	mA	
I _{FRM}	repetitive peak forward current		_	600	mA	
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4				
		t = 1 μs	_	10	Α	
		t = 100 μs	_	4	Α	
		t = 1 s	_	0.75	Α	
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	250	mW	
I _{RRM}	repetitive peak reverse current		_	600	mA	
E _{RRM}	repetitive peak reverse energy	$t_p \ge 50 \ \mu s; \ f \le 20 \ Hz; \ T_j = 25 \ ^{\circ}C$	_	5	mJ	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		_	150	°C	

Note

^{1.} Device mounted on an FR4 printed-circuit board.

General purpose controlled avalanche (double) diodes

BAS29; BAS31; BAS35

ELECTRICAL CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V _F	forward voltage	see Fig.3			
		I _F = 10 mA	_	750	mV
		I _F = 50 mA	_	840	mV
		I _F = 100 mA	_	900	mV
		I _F = 200 mA	_	1	V
		I _F = 400 mA	_	1.25	V
I _R	reverse current	see Fig.5			
		V _R = 90 V	_	100	nA
		V _R = 90 V; T _j = 150 °C	_	100	μΑ
V _{(BR)R}	reverse avalanche breakdown voltage	I _R = 1 mA	120	170	V
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6	_	35	pF
t _{rr}	reverse recovery time	when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω ; measured at I_R = 3 mA; see Fig.7	_	50	ns

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point		360	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

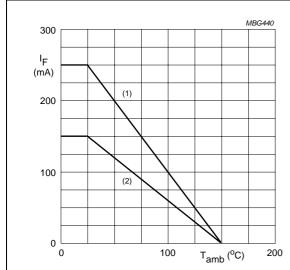
1. Device mounted on an FR4 printed-circuit board.

2003 Mar 20

General purpose controlled avalanche (double) diodes

BAS29; BAS31; BAS35

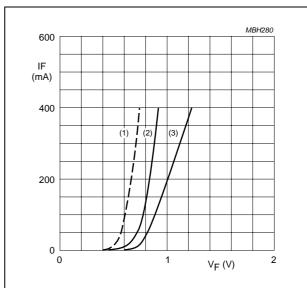
GRAPHICAL DATA



Device mounted on an FR4 printed-circuit board.

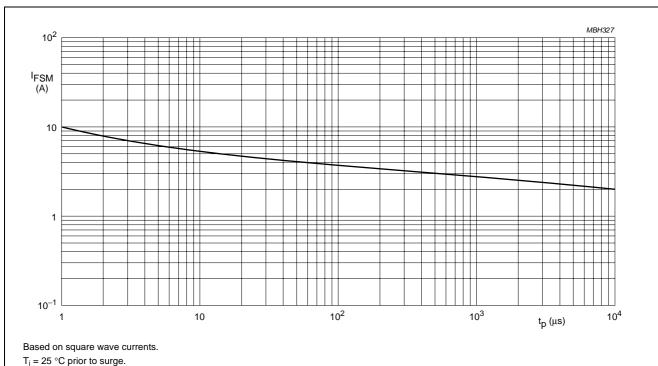
- (1) Single diode loaded.
- (2) Double diode loaded.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



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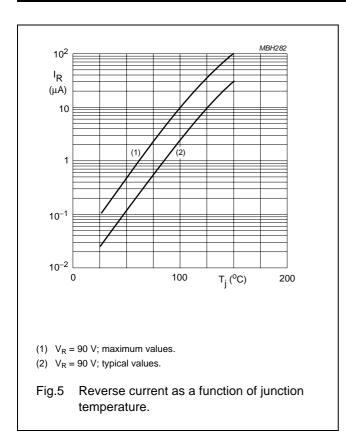
Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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General purpose controlled avalanche (double) diodes

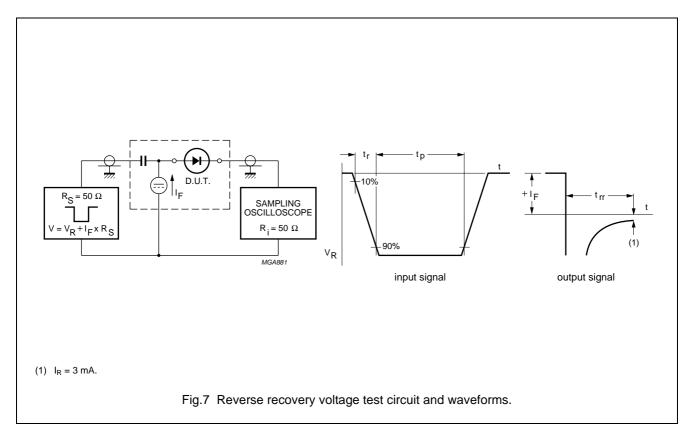
BAS29; BAS31; BAS35

MGD003



 C_{d} (pF) 30 20 I_{Q} I_{Q} I

voltage; typical values.



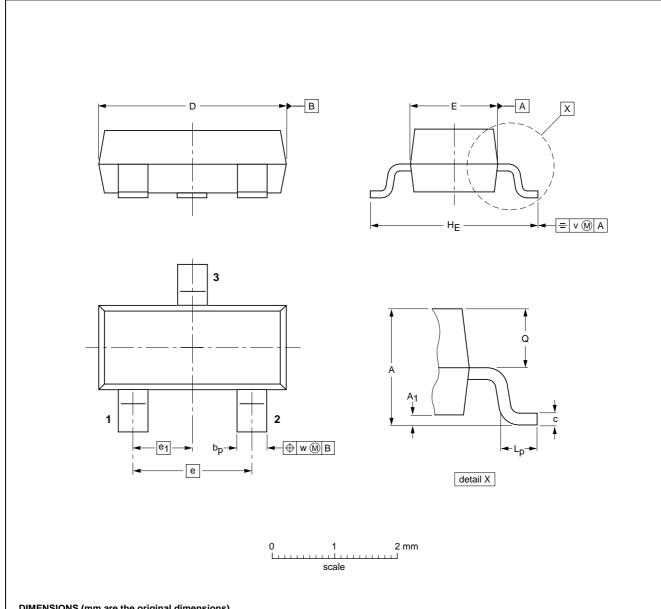
General purpose controlled avalanche (double) diodes

BAS29; BAS31; BAS35

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UN	IT	Α	A ₁ max.	bp	C	D	E	е	e ₁	HE	L _p	Q	٧	w
mr	m	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE	LINE REFERENCES					ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE	
SOT23		TO-236AB				-97-02-28- 99-09-13	

7 2003 Mar 20

General purpose controlled avalanche (double) diodes

BAS29; BAS31; BAS35

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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